

Proposal for IP block development for the Efabless 2024 Chipalooza challenge

IP Block name: *Circuit Name*
Designer/Design Team: *Name(s)*
Email address(es): *name@address, ...*
Date: *March 1, 2024*

Circuit description:

Basic circuit description from the specification. Elaborate if needed.

Circuit pinout:

Note any changes from the specification, such as if trim bits have been added.

Circuit architecture:

Describe the underlying architecture, citing any sources used. Sources must be public and may not contain patented material.

External resources (if any) (all resources must be open source):

List any resources that come from on chip, such as a bandgap-referenced voltage or PTAT current, or from other IP blocks (such as a comparator used in an ADC). List any external resources needed for testbench circuits, including any digital control sequencing needed.

Specification challenges:

List all specifications which may be difficult to attain, and what circuit design methods will be used to meet those specifications. Note where specifications will be affected by layout considerations, such as mismatch, crosstalk, and I-R drop.

Testbenches required for verifying circuit performance:

List what testbenches are used for each of the electrical parameters to be tested, and briefly describe the testbench circuit setup and how it measures the specified parameter.

Connections required for standalone (breakout) implementation:

Indicate how the circuit is to be connected for individual testing outside of the eventual SoC application, and where test points may need to be added to access internal states of the circuit. Note where pad capacitance, wirebond inductance, and wire resistance from pad to circuit may affect measurement, and how to mitigate. Note where the circuit may need to be placed as close as possible to a pad.

Test plan for standalone (breakout) implementation:

Describe how the standalone circuit can be measured on a lab bench to verify that the circuit meets performance requirements for each specified electrical parameter.